

#### **PART OSBOLETE - USE DGD05473**



DGD0547

#### HIGH FREQUENCY HIGH-SIDE AND LOW-SIDE GATE DRIVER IN W-DFN3030-10

#### **Description**

The DGD0547 is a high-frequency gate driver capable of driving N-channel MOSFETs. The floating high-side driver is rated up to 50V.

The DGD0547 logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) to interface easily with MCUs. UVLO for high-side and low-side will protect a MOSFET with loss of supply. To protect MOSFETs, cross conduction prevention logic prevents the HO and LO outputs from being on at the same time.

Fast and well-matched propagation delays allow a higher switching frequency, enabling a smaller, more compact power switching design, using smaller associated components. To minimize space an internal bootstrap diode is included. The DGD0547 is offered in the W-DFN3030-10 (Type TH) package and operates over an extended - 40°C to +125°C temperature range.

#### **Applications**

- DC-DC Converters
- Motor Controls
- Battery Powered Hand Tools
- eCig Devices
- Class D Power Amplifiers

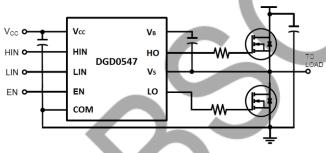
#### **Features**

- 50V Floating High-Side Driver
- Drives Two N-channel MOSFETs in a Half-Bridge Configuration
- 1.5A Source / 2.5A Sink Output Current Capability
- Internal Bootstrap Diode Included
- Undervoltage Lockout for High-Side and Low-Side Drivers
- Delay Matching Maxmimum of 5ns
- Propagation Delay Typical of 20ns
- Logic Input (HIN, LIN and EN) 3.3V Capability
- Ultra Low Standby Currents (<1µA)</li>
- Extended Temperature Range: -40°C to +125°C
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

#### **Mechanical Data**

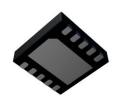
- Case: W-DFN3030-10
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminals: Finish Matte Tin Finish
- Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.017 grams (Approximate)







Top View



**Bottom View** 

W-DFN3030-10 (Type TH)

#### Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DGD0547FN-7	DGD0547	7	8	3,000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

## **Marking Information**

Notes:

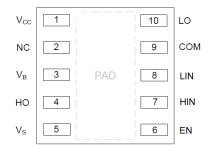
Downloaded from **Arrow.com**.



DGD0547 = Product Type Marking Code YY = Year (ex: 21 = 2021) WW = Week (01 to 53)



# Pin Diagrams

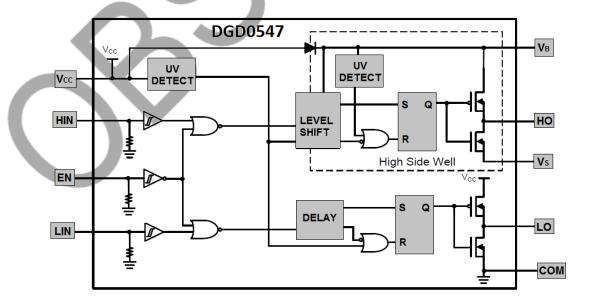


Top View: W-DFN3030-10 (Type TH)

## **Pin Descriptions**

Pin Number	Pin Name	Function
1	Vcc	Low-Side and Logic Supply
2	NC	No Connect (No Internal Connection)
3	VB	High-Side Floating Supply
4	НО	High-Side Gate Drive Output
5	Vs	High-Side Floating Supply Return
6	EN	Logic Input Enable, a Logic Low turns off Gate Driver
7	HIN	Logic Input for High-Side Gate Driver, in Phase with HO
8	LIN	Logic Input for Low-Side Gate Driver, in Phase with LO
9	COM	Low-Side and Logic Return
10	LO	Low-Side Gate Drive Output
PAD	Substrate	Connect to COM on PCB

## **Functional Block Diagram**





## **Absolute Maximum Ratings** (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
High-Side Floating Positive Supply Voltage	V <sub>B</sub>	-0.3 to +60	V
High-Side Floating Negative Supply Voltage	Vs	V <sub>B</sub> -14 to V <sub>B</sub> +0.3	V
High-Side Floating Output Voltage	Vно	Vs-0.3 to V <sub>B</sub> +0.3	V
Offset Supply Voltage Transient	dVs / dt	50	V/ns
Logic and Low-Side Fixed Supply Voltage	V <sub>CC</sub>	-0.3 to +14	V
Low-Side Output Voltage	VLO	-0.3 to V <sub>CC</sub> +0.3	V
Logic Input Voltage (HIN, LIN and EN)	Vin	-0.3 to Vcc+0.3	V
Bootstrap Diode Current (Pulsed <10µs)	I <sub>BD</sub>	1	А

#### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor (Note 5)	PD	0.4	W
Thermal Resistance, Junction to Ambient (Note 5)	Reja	64	°C/W
Thermal Resistance, Junction to Case (Note 5)	Rejc	42	°C/W
Operating Temperature	TJ	+150	
Lead Temperature (Soldering, 10s)	TL	+300	°C
Storage Temperature Range	Tstg	-55 to +150	

Note:

5. When mounted on a standard JEDEC 2-layer FR-4 board.

## **Recommended Operating Conditions**

Parameter	Symbol	Min	Max	Unit
High-Side Floating Supply	V <sub>B</sub>	Vs + 5	V <sub>S</sub> + 14	V
High-Side Floating Supply Offset Voltage	Vs	(Note 6)	50 (Note 7)	V
High-Side Floating Output Voltage	Vно	Vs	VB	V
Logic and Low Side Fixed Supply Voltage	Vcc	5	14	V
Low-Side Output Voltage	VLO	0	Vcc	V
Logic Input Voltage (HIN, LIN and EN)	Vin	0	5	V
Ambient Temperature	TA	-40	+125	°C

Notes:

- 6. Logic operation for Vs of -5V to +50V.
- 7. Provided V<sub>B</sub> doesn't exceed absolute maximum rating of 60V.



## DC Electrical Characteristics (V<sub>CC</sub> = V<sub>BS</sub> = 12V, COM = V<sub>S</sub> = 0V, @T<sub>A</sub> = +25°C, unless otherwise specified.) (Note 8)

Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Logic "1" Input Voltage	ViH	2.4	-	1	V	_
Logic "0" Input Voltage	VIL	_	-	8.0	V	-
Enable Logic "1" Input Voltage	VENIH	1.6	-	-	V	-
Enable Logic "0" Input Voltage	VENIL	_	_	0.7	V	-
Input Voltage Hysteresis	V <sub>INHYS</sub>	_	0.6	-	V	-
Enable Input Voltage Hysteresis	VENINHYS	_	0.1	1	٧	_
High Level Output Voltage, VBIAS - VO	Voн	_	0.45	0.6	V	I <sub>O+</sub> = 100mA
Low Level Output Voltage, Vo	$V_{OL}$	_	0.15	0.22	V	I <sub>O-</sub> = 100mA
Offset Supply Leakage Current	I <sub>LK</sub>	_	1	5	μΑ	$V_B = V_S = 60V$
Vcc Shutdown Supply Current	Iccsd	_	0	1	μΑ	$V_{IN} = 0V \text{ or } 5V, V_{EN} = 0V$
Vcc Quiescent Supply Current	Iccq	_	130	200	μΑ	$V_{IN} = 0V \text{ or } 5V$
Vcc Operating Supply Current	Іссор	_	7.3	ď	mA	fs = 500kHz
V <sub>BS</sub> Quiescent Supply Current	I <sub>BSQ</sub>	_	40	100	μΑ	VIN = 0V  or  5V
V <sub>BS</sub> Operating Supply Current	IBSOP	_	7.3	-	mA	fs = 500kHz
Logic "1" Input Bias Current	I <sub>IN+</sub>	_		50	μA	$V_{IN} = 5V$
Logic "0" Input Bias Current	I <sub>IN</sub> -	- /	_	5	μΑ	$V_{IN} = 0V$
Enable Logic "1" Input Bias Current	I <sub>ENIN+</sub>	-	43	60	μΑ	VIN = 5V
Enable Logic "0" Input Bias Current	I <sub>ENIN</sub> -	-	0	5	μΑ	$V_{IN} = 0V$
V <sub>BS</sub> Supply Undervoltage Positive Going Threshold	V <sub>BSUV+</sub>	4.1	4.5	4.9	<b>V</b>	_
V <sub>BS</sub> Supply Undervoltage Negative Going Threshold	V <sub>BSUV</sub> -	3.6	4.0	4.4	>	_
Vcc Supply Undervoltage Positive Going Threshold	Vccuv+	4.1	4.5	4.9	V	_
Vcc Supply Undervoltage Negative Going Threshold	Vccuv-	3.6	4.0	4.4	V	_
Output High Short Circuit Pulsed Current	I <sub>O+</sub>	1.0	1.5	_	Α	V <sub>O</sub> = 0V, PW ≤ 10μs
Output Low Short Circuit Pulsed Current	lo-	1.9	2.5	1	Α	Vo = 15V, PW ≤ 10µs
Forward Voltage of Bootstrap Diode	V <sub>F1</sub>	1	0.67	1	V	$I_F = 100\mu A$
Forward Voltage of Bootstrap Diode	V <sub>F2</sub>		1.2	-	V	I <sub>F</sub> = 100mA

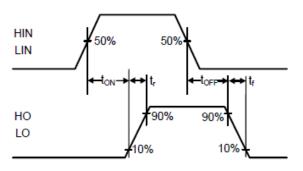
Note: 8. The V<sub>IN</sub> and I<sub>IN</sub> parameters are applicable to the two logic pins: HIN, LIN and EN. The V<sub>O</sub> and I<sub>O</sub> parameters are applicable to the respective output pins: HO and LO.

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Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Turn-On Propagation Delay	ton	-	20	35	ns	_
Turn-Off Propagation Delay	toff	_	23	56	ns	Vs = 50V
Delay Matching, HO & LO Turn-On	t <sub>DM</sub>	_	_	5	ns	-
Turn-On Rise Time	t <sub>R</sub>	_	16	30	ns	_
Turn-Off Fall Time	t <sub>F</sub>	_	12	25	ns	_



## **Timing Waveforms**



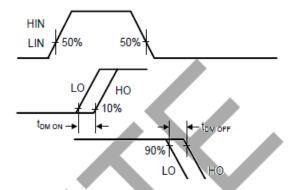


Figure 1. Switching Time Waveform Definitions

Figure 2. Delay Matching Waveform Definitions

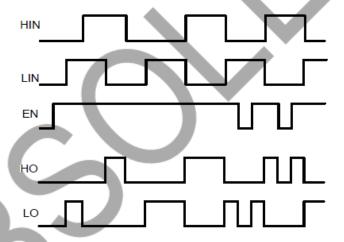


Figure 3. Input / Output Timing Diagram



## Typical Performance Characteristics (@TA = +25°C, unless otherwise specified.)

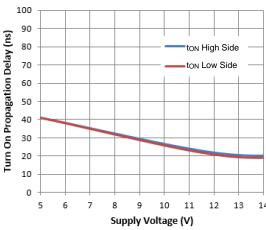


Figure 4. Turn-on Propagation Delay vs. Supply Voltage

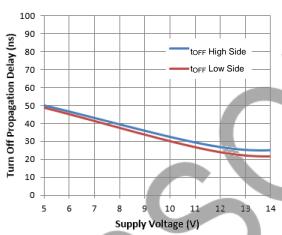


Figure 6. Turn-off Propagation Delay vs. Supply Voltage

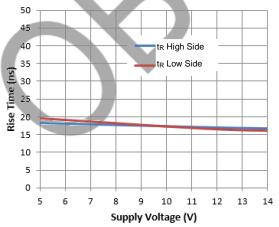


Figure 8. Rise Time vs. Supply Voltage

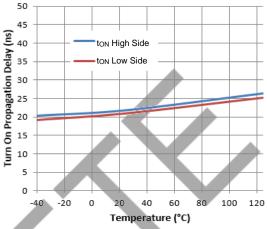


Figure 5. Turn-on Propagation Delay vs. Temperature

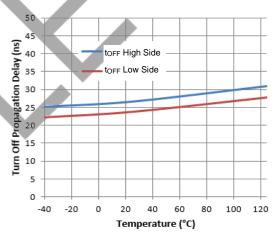


Figure 7. Turn-off Propagation Delay vs. Temperature

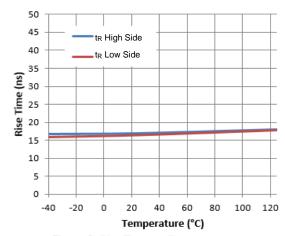


Figure 9. Rise Time vs. Temperature



## **Typical Performance Characteristics** (continued)

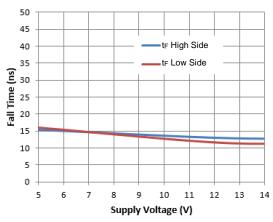


Figure 10. Fall Time vs. Supply Voltage

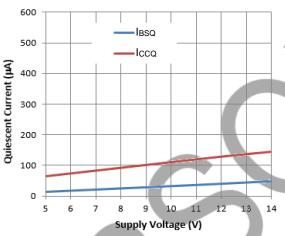


Figure 12. Quiescent Current vs. Supply Voltage

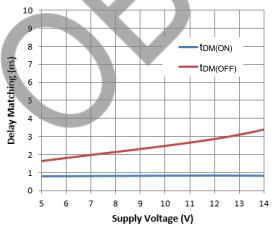


Figure 14. Delay Matching vs. Supply Voltage

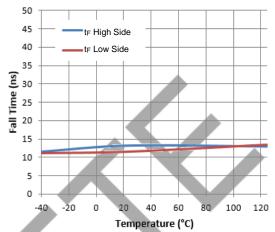


Figure 11. Fall Time vs. Temperature

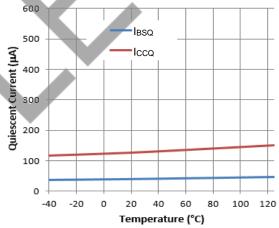


Figure 13. Quiescent Current vs. Temperature

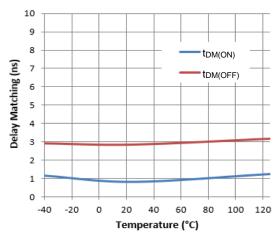


Figure 15. Delay Matching vs. Temperature



## **Typical Performance Characteristics** (continued)

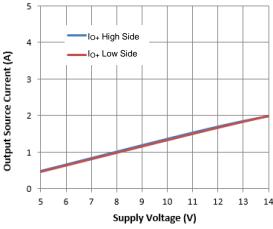


Figure 16. Output Source Current vs. Supply Voltage

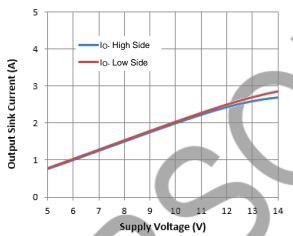


Figure 18. Output Sink Current vs. Supply Voltage

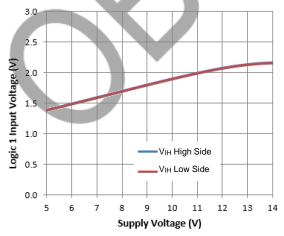


Figure 20. Logic 1 Input Voltage vs. Supply Voltage

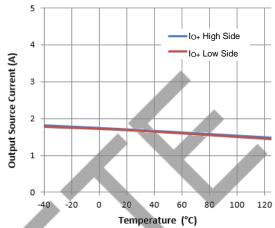


Figure 17. Output Source Current vs. Temperature

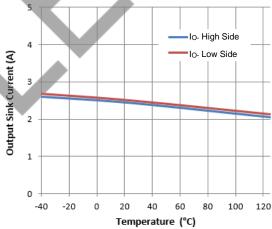


Figure 19. Output Sink Current vs. Temperature

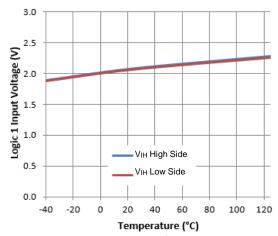


Figure 21. Logic 1 Input Voltage vs. Temperature



## **Typical Performance Characteristics** (continued)

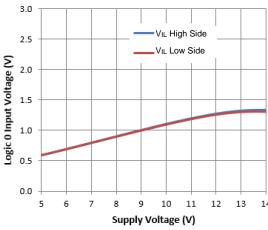


Figure 22. Logic 0 Input Voltage vs. Supply Voltage

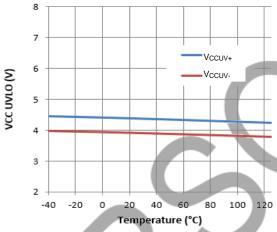


Figure 24. VCC UVLO vs. Temperature

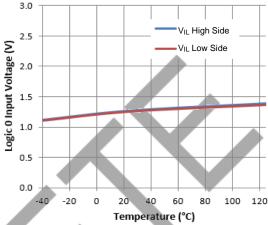


Figure 23. Logic 0 Input Voltage vs. Temperature

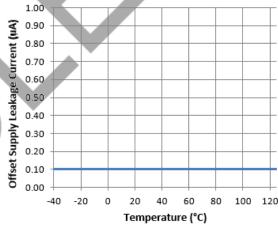


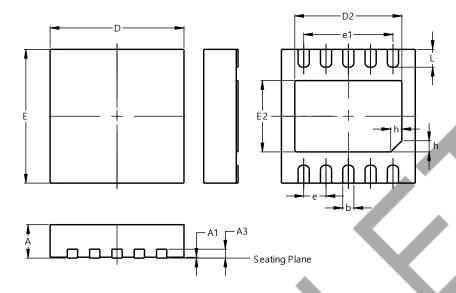
Figure 25. Offset Supply Leakage Current vs. Temperature



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### W-DFN3030-10 (Type TH)

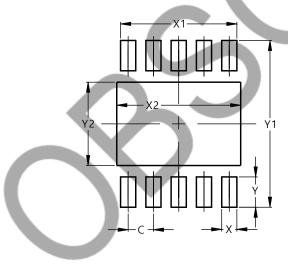


W-DFN3030-10							
	(Type TH)						
Dim	Min Max Typ						
Α	0.70	0.80	0.75				
A1		0.05	0.02				
A3	0.18	0.25	0.20				
b	0.18	0.30	0.25				
D	2.90	3.10	3.00				
D2	2.40	2.60	2.50				
е	0.50BSC						
e1		2.00BS	SC .				
E	2.90	3.10	3.00				
E2	1.45	1.65	1.55				
h <sup>™</sup>	0.20	0.30	0.25				
L	0.30	0.50	0.40				
All	All Dimensions in mm						

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

## W-DFN3030-10 (Type TH)



Dimensions	Value (in mm)		
С	0.500		
Х	0.300		
X1	2.300		
X2	2.600		
Υ	0.600		
Y1	3.300		
Y2	1.650		



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